

Features

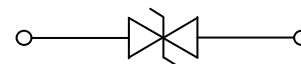
- 150W peak pulse power ($t_p = 8/20\mu s$)
- Bidirectional configurations
- Protects one I/O port
- Low clamping voltage
- Low Leakage current
- ESD-immunity acc. IEC 61000-4-2 $\pm 30kV$ contact $\pm 30kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)



DFN1006

Applications

- Cell Phone
- PDA
- Notebook
- Digital Cameras
- Portable Instrumentation
- Audio and video equipment



Schematic Diagram

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Peak Pulse Power ($T_p = 8/20\mu s$)	P_{PP}	150	W
Peak Pulse Current ($t_p = 8/20\mu s$)	I_{PP}	9.4	A
Junction Temperature	T_J	-55 To +125	$^\circ C$
Storage Temperature	T_{STG}	-55 To +150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	5.6	6.8	-	V
Reverse Leakage Current	I_R	$V_R = 5V$	-	-	1	μA
Clamping Voltage	V_C	$I_{PP} = 5A, T_p = 8/20\mu s$	-	-	11.6	V
	V_C	$I_{PP} = 9.4A, T_p = 8/20\mu s$	-	-	18.6	V
Junction Capacitance	C_J	$V_R = 0V, f = 1MHz$	-	15	-	pF

Typical Characteristic Curves

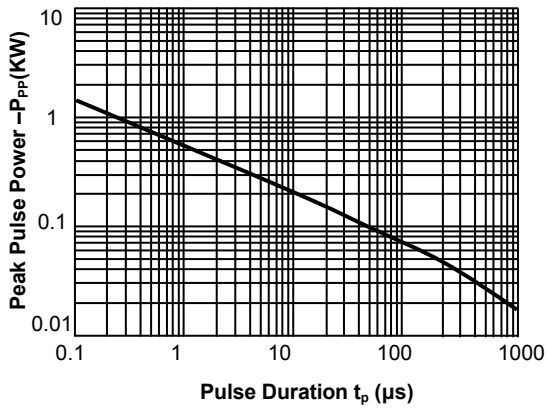


Fig.1 Peak Pulse Power Rating Curve

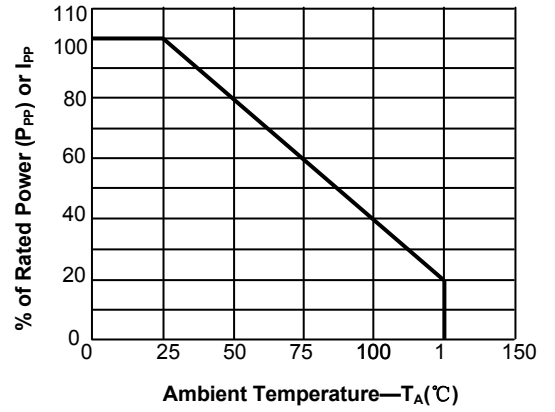


Fig.2 Pulse Derating Curve

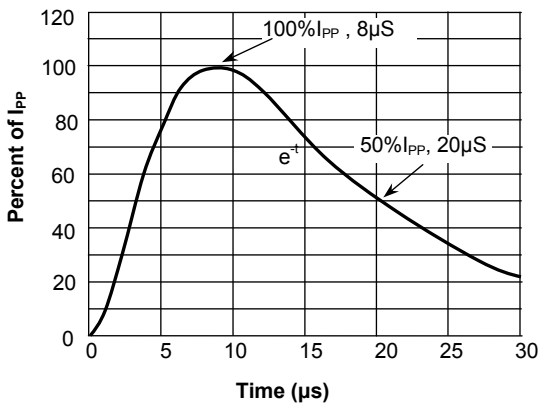


Fig.3 Pulse Waveform-8/20μs

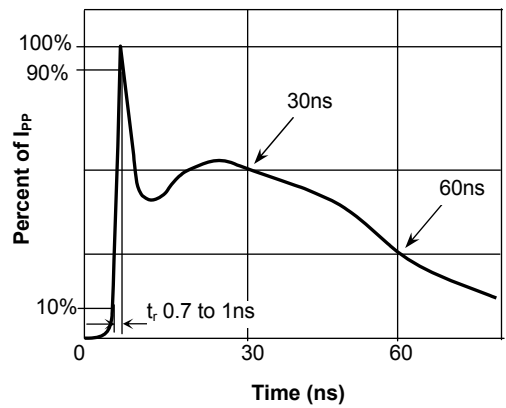
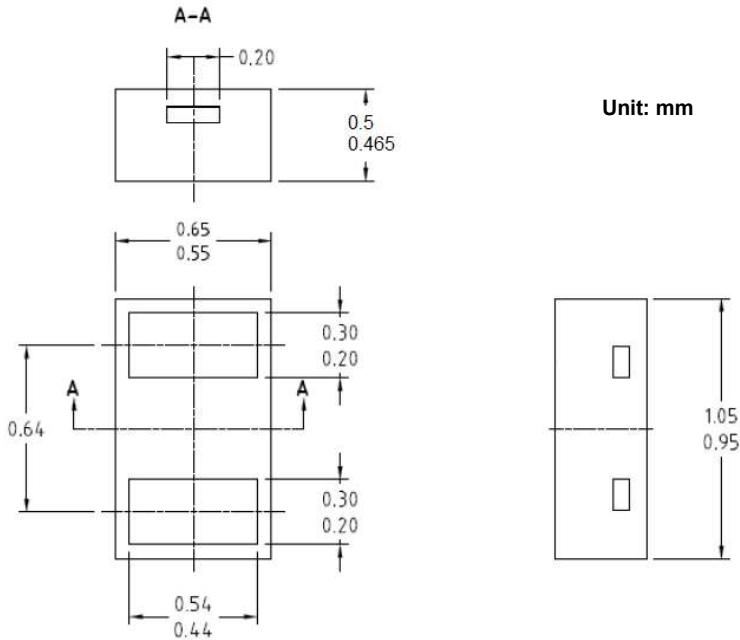


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)

Product Dimensions

DFN1006



Order Information

Device	Package	Marking	Carrier	Quantity	HSF Status
GSEZ5B159	DFN1006	C	Tape & Reel	10,000pcs / Reel	RoHS compliant